



Attorney Docket No. 740819-559

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12/9/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Shin HASHIMOTO et al.)
Application No. 09/856,823) Group Art Unit: 1765
) Examiner: Matthew J. SONG
Filed: May 25, 2001)
For: METHOD FOR FABRICATING)
SEMICONDUCTOR DEVICE)

AMENDMENT

Commissioner for Patents
Washington D.C. 20231

Sir:

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DEC 06 2002
TC 1700

In response to the Examiner's Office Action mailed August 5, 2002, the due date for which having been extended one (1) month to December 5, 2002, please consider the following amendments and remarks in connection with the above-identified application.

IN THE CLAIMS:

Please amend the claims as follows:

Claim 1. (Amended) A method for fabricating a semiconductor device comprising the steps of:

B₁ distributing a nonmetal element towards an inner portion of a substrate and in a region in the vicinity of a surface portion of a semiconductor layer;

depositing a metal film on said semiconductor layer; and

epitaxially growing a semiconductor-metal compound layer in the surface portion of said semiconductor layer by causing a reaction between an element included in said semiconductor layer and a metal included in said metal film through annealing carried out on said metal film.

B₂ Claim 9. (Amended) The method for fabricating a semiconductor device of Claim 15, wherein said oxygen has a concentration of 4×10^{14} through $4 \times 10^{15} \text{ cm}^{-2}$.